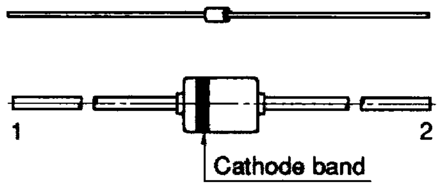
1SS110

Silicon Epitaxial Planar Diode for Tuner Band Switch

Features

- Low forward resistance. ($r_f = 0.9\Omega$ max)
- Suitable for 5mm pitch high speed automatical insertion.
- Small glass package (MHD) enables easy mounting and high reliability.

Outline



1. Cathode
2. Anode

Ordering Information

Type No.	Cathode band	Package Code
1SS110	Verdure	MHD

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	35	V
Forward current	I_F	100	mA
Power dissipation	P_d	15 0	mW
Operation temperature	T_{opr}	-20 to + 60	°C
Storage temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	1.0	V	$I_F = 10$ mA
Reverse voltage	V_R	35	—	—	V	$I_R = 10$ µA
Reverse current	I_R	—	—	0.1	µA	$V_R = 25$ V
Capacitance	C	—	—	1.2	pF	$V_R = 6$ V , f = 1 MHz
Forward resistance	r_f	—	—	0.9	Ω	$I_F = 2$ mA , f = 100 MHz

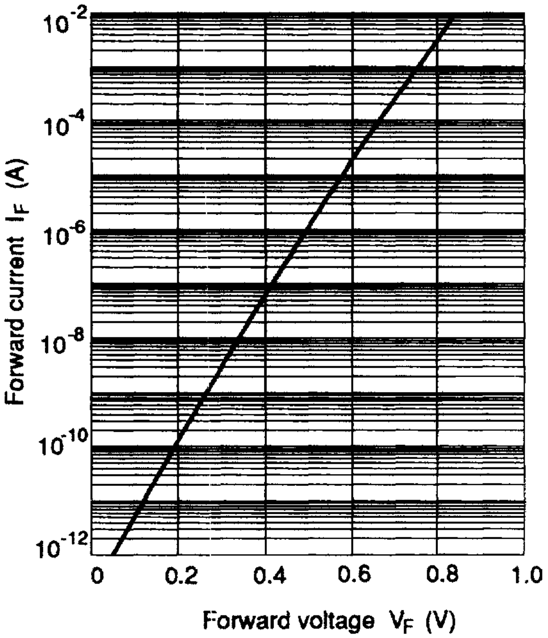


Fig.1 Forward current Vs. Forward voltage

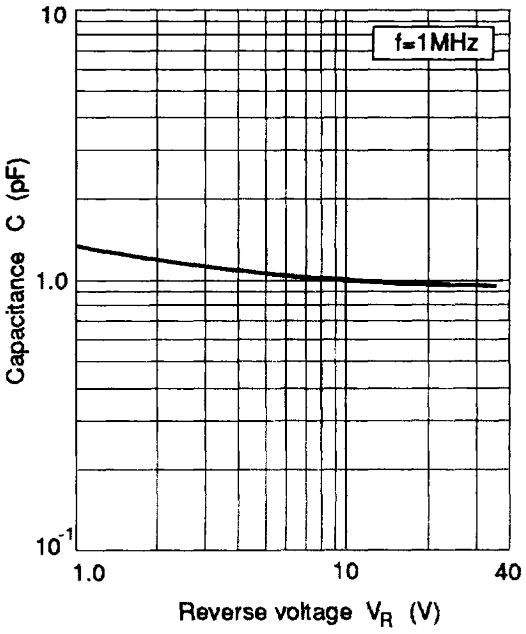


Fig.2 Capacitance Vs. Reverse voltage

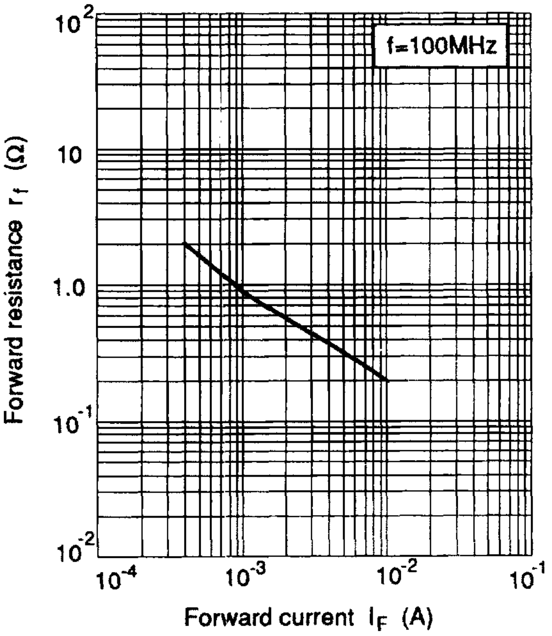


Fig.3 Forward resistance Vs. Forward current